

isc N-Channel MOSFET Transistor

18N65

FEATURES

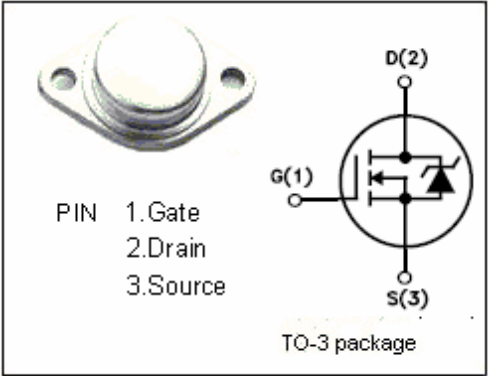
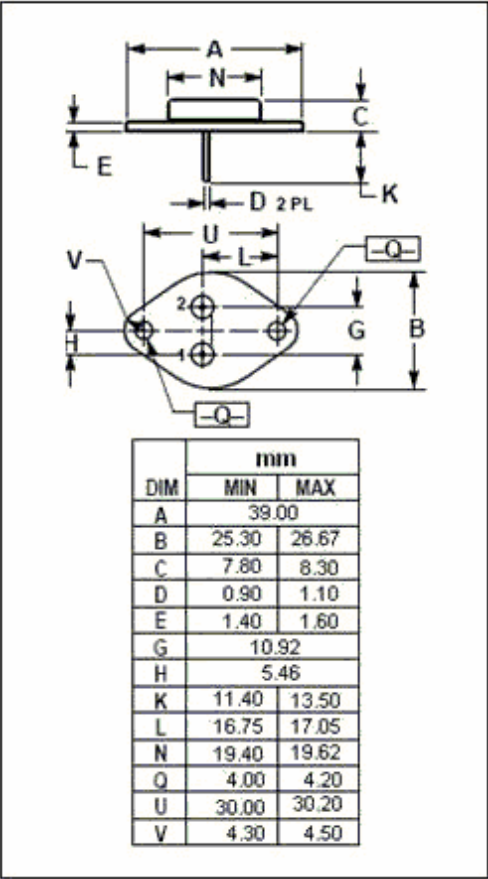
- Drain Current $I_D = 18A @ T_C = 25^{\circ}C$
- Drain Source Voltage
: $V_{DSS} = 650V (Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.4 \Omega (Max)$

APPLICATIONS

- Switching applications
- Switching converters, motor drivers, relay drivers

ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	18	A
I_{DM}	Drain Current-Single Plused	45	A
P_D	Total Dissipation @ $T_C = 25^{\circ}C$	300	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc N-Channel MOSFET Transistor**18N65****• ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	650			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	3.9		4.5	V
V_{SD}	Diode Forward On-voltage	$I_S=18\text{A}; V_{GS}=0$			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=9\text{A}$			0.4	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650\text{V}; V_{GS}=0$			250	μA